

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	72801	(thin: near film: near transistor) or TFT	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/21 13:31
L2	47322	(gate near electrode) same ((gate near insulat\$3) or (gate near dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/21 13:32
L3	75352	(impurity or dopant or carrier or doping) near concentration	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/21 13:34
L4	14941	I1 and I2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/21 13:35
L6	8708	I4 and (semiconductor near (layer or region))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/21 13:38
L7	2183	I6 and I3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/21 13:36
L8	9	I4 and (energy near bandgap)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/21 13:38
L9	12449	AlGaAs and GaAs	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/21 13:39
L10	18	I4 and I9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/21 13:40